

**AMENDMENT**

**IN THE CLAIMS:**

Please amend the claims as follows:

1. (Original) A manufacturing method of a semiconductor device, comprising the steps of:
  - depositing on a substrate a dielectric film made of fluorine-added carbon;
  - forming on the dielectric film a protective layer comprising a nitrogen-added silicon carbide film; and
  - depositing on the protective layer a thin film serving as a hardmask made of oxygen-added silicon carbide by a plasma containing active species of silicon, carbon, and oxygen.
2. (Currently amended) The manufacturing method according to claim 1, wherein
  - the plasma containing active species of silicon, carbon, and oxygen is ~~a plasma~~ obtained by activating a gas of an organic silicon compound and an oxygen gas.
3. (Currently amended) The manufacturing method according to claim 1, wherein
  - the step of forming the protective layer includes the sub-steps of:
    - depositing on the dielectric film a silicon carbide film by a second plasma containing active species of silicon and carbon; and
    - depositing on the silicon carbide ~~film~~ a film the nitrogen-added silicon carbide film by a third plasma containing active species of silicon, carbon, and nitrogen.
4. (Currently amended) The manufacturing method according to claim 1, wherein
  - the step of forming the protective layer includes the sub-steps of:
    - depositing on the dielectric film a silicon carbide film by a second plasma obtained by activating a gas of an organic silicon compound; and
    - depositing on the silicon carbide ~~film~~ a film the nitrogen-added silicon carbide film by a third plasma containing active species of an organic silicon compound and active species of nitrogen.

5. (Currently amended) The manufacturing method according to claim 1, further comprising the steps of:

forming on the thin film serving as a ~~hardmask~~ the hardmask, a resist film having a specific first pattern;

etching the thin film by a second plasma through the resist film to obtain a ~~hardmask~~ the hardmask having a second pattern corresponding to ~~that of the resist film~~ the first pattern; and

etching the dielectric film by a third plasma through the hardmask.

6-12. (Canceled)